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(57)

ABSTRACT

A semiconductor device includes a first conductive layer, a memory layer, a second conductive layer and a selector layer. The memory layer surrounds the first conductive layer. The second conductive layer is disposed aside the memory layer. The selector layer is disposed on the second conductive layer. A first side of the second conductive layer is covered by the memory layer, a second side of the second conductive layer is covered by the selector layer, and a third side of the second conductive layer is exposed by the selector layer.

